

ZX5T3Z

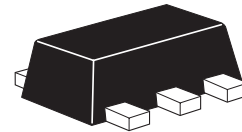
40V PNP HIGH GAIN LOW SATURATION MEDIUM POWER TRANSISTOR IN SOT89

SUMMARY

$BV_{CEO} = -40V$; $R_{SAT} = 29m\Omega$; $I_C = -5.5A$

DESCRIPTION

Packaged in the SOT89 outline this new 5th generation low saturation 40V PNP transistor offers low on state losses making it ideal for use in DC-DC circuits, line switching and particularly charging circuits.



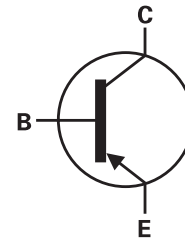
SOT89

FEATURES

- Extremely low equivalent on-resistance
- 5.5 amps continuous current
- Up to 15 amps peak current
- Very low saturation voltages < -60mV @ -1A

APPLICATIONS

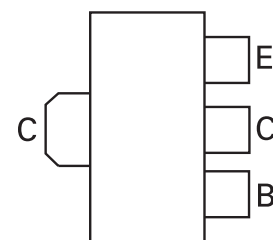
- Charging circuits
- DC - DC converters
- MOSFET gate drivers
- Power switches
- Motor control



ORDERING INFORMATION

| DEVICE | REEL SIZE | TAPE WIDTH | QUANTITY PER REEL |
|----------|-----------|------------|-------------------|
| ZX5T3ZTA | 7" | 12mm | 1000 units |

PINOUT



TOP VIEW

DEVICE MARKING

- 53Z

ZX5T3Z

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | LIMIT | UNIT |
|--|----------------|------------|----------------------|
| Collector-base voltage | BV_{CBO} | -50 | V |
| Collector-base voltage | BV_{CBS} | -50 | V |
| Collector-emitter voltage | BV_{CEO} | -40 | V |
| Emitter-base voltage | BV_{EBO} | -7.5 | V |
| Continuous collector current ^(b) | I_C | -5.5 | A |
| Peak pulse current | I_{CM} | -15 | A |
| Power dissipation at $T_A = 25^\circ\text{C}$ ^(a) | P_D | 0.9 | W |
| Linear derating factor | | 7.2 | mW/ $^\circ\text{C}$ |
| Power dissipation at $T_A = 25^\circ\text{C}$ ^(b) | P_D | 1.5 | W |
| Linear derating factor | | 12 | mW/ $^\circ\text{C}$ |
| Power dissipation at $T_A = 25^\circ\text{C}$ ^(c) | P_D | 2.1 | W |
| Linear derating factor | | 16.8 | mW/ $^\circ\text{C}$ |
| Power dissipation at $T_A = 25^\circ\text{C}$ ^(d) | P_D | 3 | W |
| Linear derating factor | | 24 | mW/ $^\circ\text{C}$ |
| Operating and storage temperature range | T_j, T_{stg} | -55 to 150 | $^\circ\text{C}$ |

THERMAL RESISTANCE

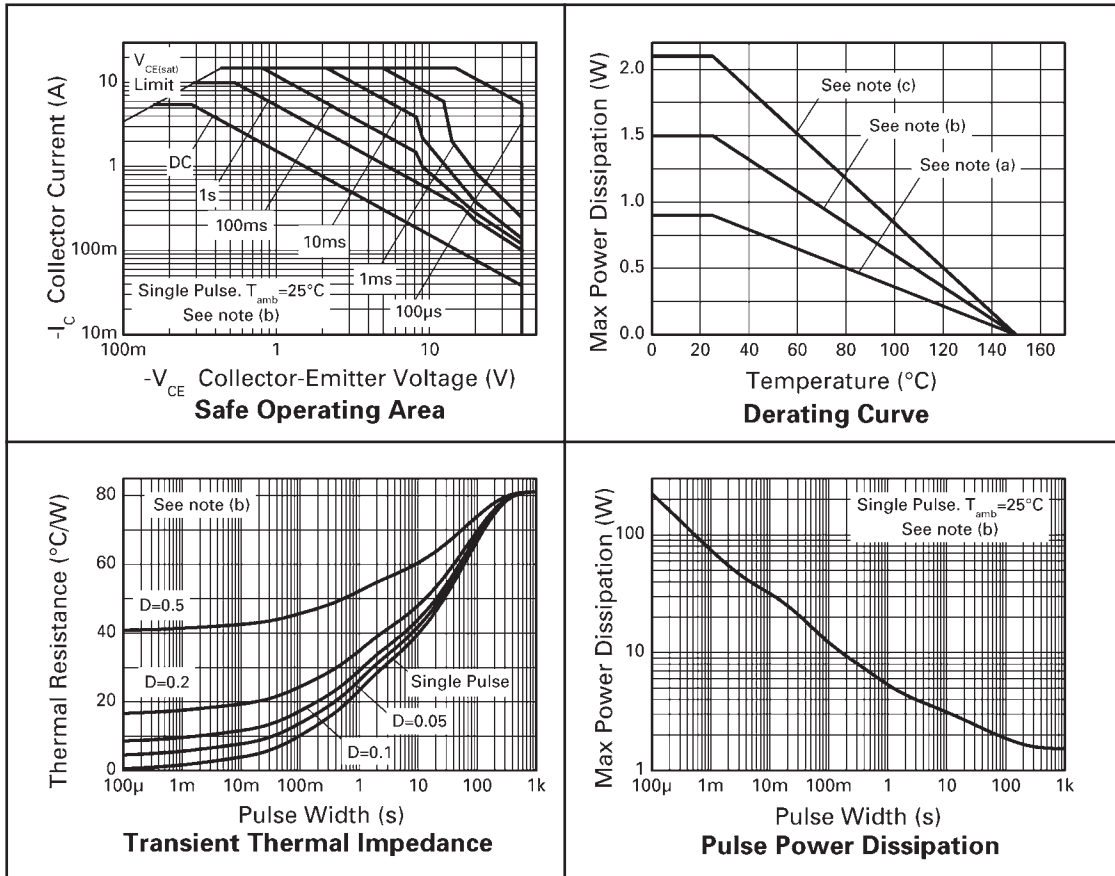
| PARAMETER | SYMBOL | VALUE | UNIT |
|------------------------------------|-----------------|-------|---------------------------|
| Junction to ambient ^(a) | $R_{\theta JA}$ | 139 | $^\circ\text{C}/\text{W}$ |
| Junction to ambient ^(b) | $R_{\theta JA}$ | 83 | $^\circ\text{C}/\text{W}$ |
| Junction to ambient ^(c) | $R_{\theta JA}$ | 60 | $^\circ\text{C}/\text{W}$ |
| Junction to ambient ^(d) | $R_{\theta JA}$ | 42 | $^\circ\text{C}/\text{W}$ |

NOTES

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
(b) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
(c) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
(d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB measured at $t < 5$ secs.

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CHARACTERISTICS



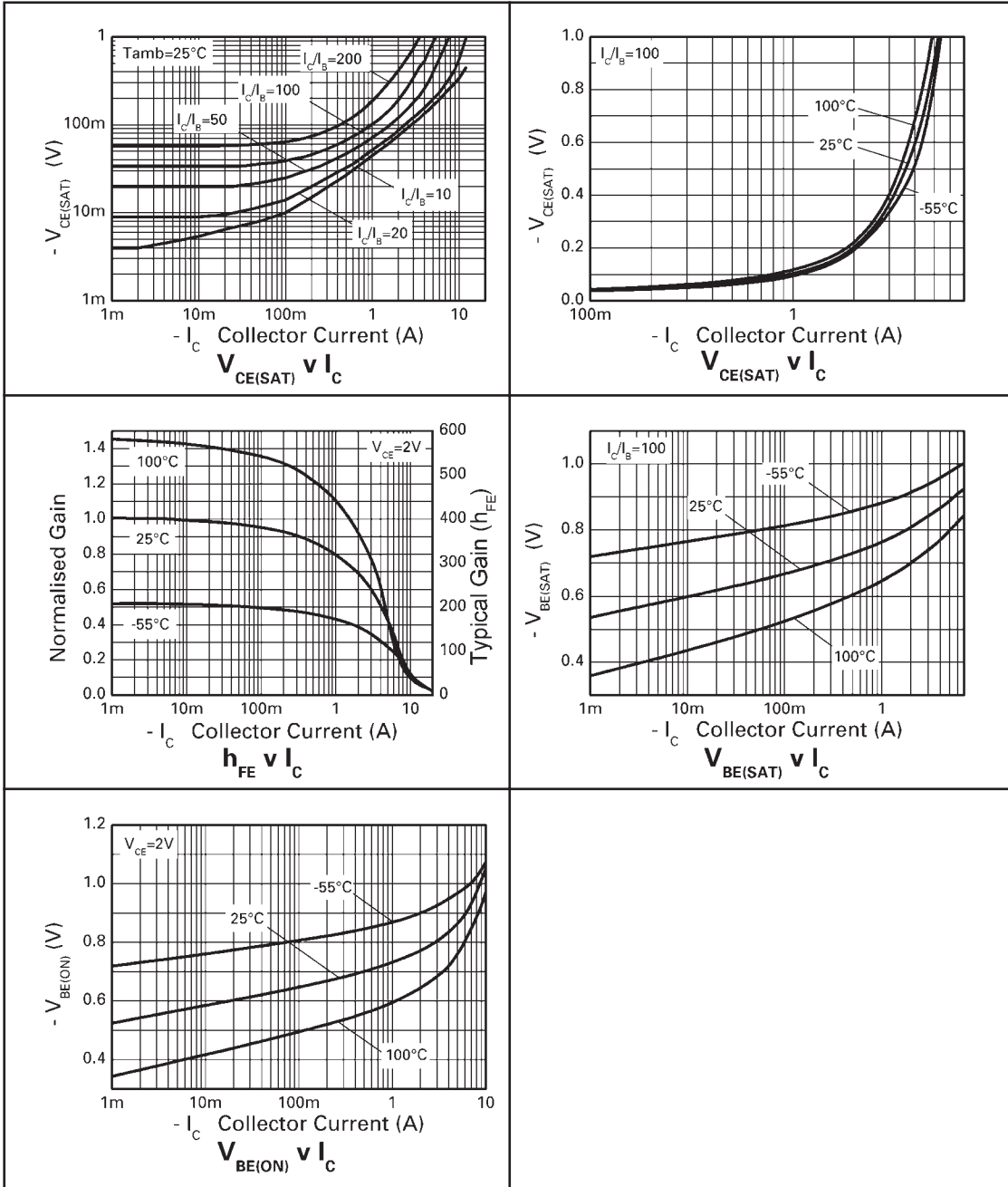
ZX5T3Z

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | CONDITIONS |
|---------------------------------------|----------------------------------|------|-------|---|------|--|
| Collector-base breakdown voltage | BV_{CBO} | -50 | -90 | | V | $I_C = -100\mu\text{A}$ |
| Collector-emitter breakdown voltage | BV_{CES} | -50 | -90 | | V | $I_C = -100\mu\text{A}$ |
| Collector-emitter breakdown voltage | BV_{CEO} | -40 | -58 | | V | $I_C = -10\text{mA}^*$ |
| Emitter-base breakdown voltage | BV_{EBO} | -7.5 | -8.3 | | V | $I_E = -100\mu\text{A}$ |
| Collector cut-off current | I_{CBO} | | <1 | -20 | nA | $V_{CB} = -40\text{V}$ |
| Collector cut-off current | I_{CES} | | <1 | -20 | nA | $V_{CB} = -32\text{V}$ |
| Emitter cut-off current | I_{EBO} | | <1 | -20 | nA | $V_{EB} = -6\text{V}$ |
| Collector-emitter saturation voltage | $V_{CE(SAT)}$ | | -15 | -30 | mV | $I_C = -0.1\text{A}, I_B = -10\text{mA}^*$ |
| | | | -44 | -60 | mV | $I_C = -1\text{A}, I_B = -100\text{mA}^*$ |
| | | | -50 | -70 | mV | $I_C = -1\text{A}, I_B = -50\text{mA}^*$ |
| | | | -120 | -165 | mV | $I_C = -1\text{A}, I_B = -10\text{mA}^*$ |
| | | | -70 | -80 | mV | $I_C = -2\text{A}, I_B = -200\text{mA}^*$ |
| | | | -125 | -175 | mV | $I_C = -2\text{A}, I_B = -40\text{mA}^*$ |
| | | | -130 | -175 | mV | $I_C = -3.5\text{A}, I_B = -175\text{mA}^*$ |
| | -162 | -185 | mV | $I_C = -5.5\text{A}, I_B = -550\text{mA}^*$ | | |
| Base-emitter saturation voltage | $V_{BE(SAT)}$ | | -820 | -900 | mV | $I_C = -2\text{A}, I_B = -40\text{mA}^*$ |
| | | | -1000 | -1075 | mV | $I_C = -5.5\text{A}, I_B = -550\text{mA}^*$ |
| Base-emitter turn-on voltage | $V_{BE(ON)}$ | | -778 | -850 | mV | $I_C = -2\text{A}, V_{CE} = -2\text{V}^*$ |
| | | | -869 | -950 | mV | $I_C = -5.5\text{A}, V_{CE} = -2\text{V}^*$ |
| Static forward current transfer ratio | H_{FE} | 200 | 390 | | | $I_C = -10\text{mA}, V_{CE} = -2\text{V}^*$ |
| | | 200 | 350 | 550 | | $I_C = -0.5\text{A}, V_{CE} = -2\text{V}^*$ |
| | | 170 | 290 | | | $I_C = -2\text{A}, V_{CE} = -2\text{V}^*$ |
| | | 110 | 175 | | | $I_C = -5.5\text{A}, V_{CE} = -2\text{V}^*$ |
| Transition frequency | f_T | | 152 | | MHz | $I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$ |
| Output capacitance | C_{OBO} | | 53 | | pF | $V_{CB} = -10\text{V}, f = 1\text{MHz}^*$ |
| Switching times | t_d t_r t_s t_r | | 18 | | ns | $I_C = -1\text{A}, V_{CC} = -10\text{V},$ $I_{B1} = I_{B2} = -100\text{mA}$ |
| | | | 17 | | | |
| | | | 325 | | | |
| | | | 60 | | | |
| Switching times | t_d t_r t_s t_r | | 55 | | ns | $I_C = -2\text{A}, V_{CC} = -30\text{V},$ $I_{B1} = I_{B2} = -20\text{mA}$ |
| | | | 107 | | | |
| | | | 264 | | | |
| | | | 103 | | | |

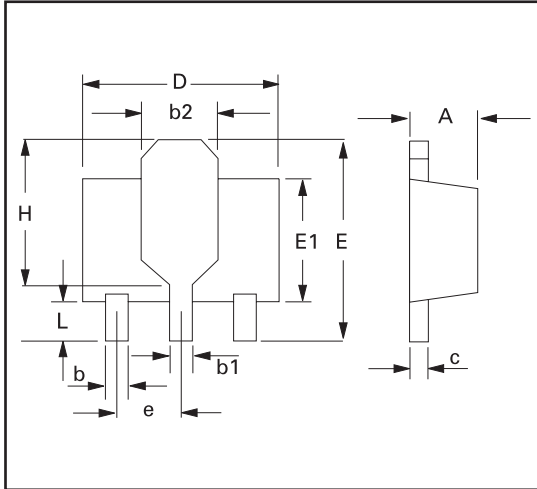
* Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS

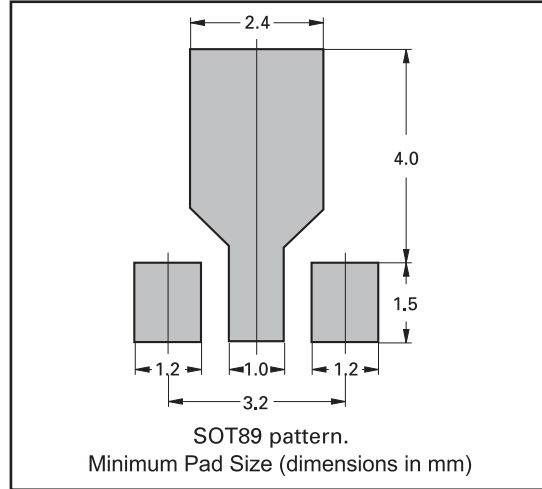


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PACKAGE OUTLINE



PAD LAYOUT DETAILS



Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

| DIM | Millimeters | | Inches | | DIM | Millimeters | | Inches | |
|-----|-------------|------|--------|-------|-----|-------------|------|--------|-------|
| | Min | Max | Min | Max | | Min | Max | Min | Max |
| A | 1.40 | 1.60 | 0.550 | 0.630 | e | 1.40 | 1.50 | 0.055 | 0.059 |
| b | 0.38 | 0.48 | 0.015 | 0.019 | E | 3.75 | 4.25 | 0.150 | 0.167 |
| b1 | - | 0.53 | - | 0.021 | E1 | - | 2.60 | - | 0.102 |
| b2 | 1.50 | 1.80 | 0.060 | 0.071 | G | 2.90 | 3.00 | 0.114 | 0.118 |
| c | 0.28 | 0.44 | 0.011 | 0.017 | H | 2.60 | 2.85 | 0.102 | 0.112 |
| D | 4.40 | 4.60 | 0.173 | 0.181 | - | - | - | - | - |

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